

U.S.S.N. 10/810,912

In the Claims

Please cancel Claims 2-4, 7-9 and 11-13 without prejudice.

Please amend Claims 1, 5 and 10.

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Listing of Claims

1. (currently amended) A method of seasoning a process chamber having interior surfaces to reduce the formation of silicon residues on said interior surfaces in a subsequent silicon plasma deposition process, comprising the steps of:

cleaning said process chamber according to a cleaning process comprising a chlorine containing etchant to remove silicon residues from said chamber; and

providing a seasoning film ~~selected from the group consisting of silicon nitride,~~ comprises silicon carbide, and ~~silicon dioxide~~ on said interior surfaces of said process chamber ~~comprising by~~ introducing precursor gases ~~selected from the group consisting of silane, dichlorosilane, and~~ comprises trimethylsilane and carbon dioxide into said process chamber at a pressure of from about 10 Torr to about 760 Torr.

Claims 2-4 (canceled)

5. (currently amended)) A method of seasoning a chemical vapor deposition chamber having interior surfaces and a gas distribution plate to reduce the formation of silicon residues on

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said interior surfaces and said gas distribution plate in a subsequent silicon plasma deposition process, comprising the steps of:

cleaning said chamber according to a cleaning process comprising a chlorine containing etchant gas to remove silicon residues from said chamber; and

providing a seasoning film ~~selected from the group consisting of silicon nitride,~~ comprises silicon carbide, ~~and silicon dioxide~~ having a thickness of from about 2  $\mu\text{m}$  to about 10  $\mu\text{m}$  on said interior surfaces and said gas distribution plate of said chamber ~~comprising by~~ introducing precursor gases ~~selected from the group consisting of silane, dichlorosilane, and~~ comprises trimethylsilane and carbon dioxide into said process chamber at a chamber pressure of from about 10 Torr to about 760 Torr at a temperature from about 500 degrees C to about 700 degrees C.

Claims 6-9 (canceled)

10. (currently amended) A method of seasoning a chemical vapor deposition chamber having interior surfaces and a gas distribution plate to reduce the formation of silicon residues on

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said interior surfaces and said gas distribution plate in a subsequent silicon plasma deposition process, comprising the steps of:

cleaning said chamber according to a cleaning process comprising a chlorine containing etchant gas to remove silicon residues from said chamber; and

providing a seasoning film ~~selected from the group consisting of silicon nitride,~~ comprises silicon carbide, ~~and silicon dioxide~~ having a thickness of from about 2  $\mu\text{m}$  to about 10  $\mu\text{m}$  on said interior surfaces and said gas distribution plate of said chamber comprising introducing precursor gases ~~selected from the group consisting of silane, dichlorosilane, and~~ comprises trimethylsilane and carbon dioxide into said process chamber at a chamber pressure of from about 10 Torr to about 760 Torr at a temperature from about 500 degrees C to about 700 degrees C and a process time of from about 0.5 minutes to about 10 minutes.

Claims 11-14 (canceled)

15. (previously presented) The method of claim 1, further comprising the step of depositing a silicon layer on a substrate within said chamber according to a plasma deposition process.

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16. (previously presented) The method of claim 15, wherein said silicon comprises amorphous silicon.

17. (canceled)

18. (previously presented) The method of claim 5, further comprising the step of depositing a silicon layer on a substrate within said chamber according to a plasma deposition process.

19. (canceled)

20. (previously presented) The method of claim 10, further comprising the step of depositing a silicon layer on a substrate within said chamber according to a plasma deposition process.